

P-CHANNEL ENHANCEMENT MODE VERTICAL DMOS FET

ZVP4424C

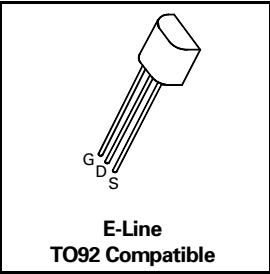
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FEATURES

- * 240 Volt V_{DS}
- * $R_{DS(on)}=9\Omega$
- * Low threshold

APPLICATIONS

- * Electronic Hook Switch



REFER TO ZVP4424A FOR GRAPHS

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Drain-Source Voltage	V_{DS}	-240	V
Continuous Drain Current at $T_{amb}=25^{\circ}C$	I_D	-200	mA
Pulsed Drain Current	I_{DM}	-1	A
Gate Source Voltage	V_{GS}	± 40	V
Power Dissipation at $T_{amb}=25^{\circ}C$	P_{tot}	750	mW
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +150	$^{\circ}C$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	TYP	MAX.	UNIT	CONDITIONS.
Drain-Source Breakdown Voltage	BV_{DSS}	-240			V	$I_D=-1mA, V_{GS}=0V$
Gate-Source Threshold Voltage	$V_{GS(th)}$	-0.7	-1.4	-2.0	V	$I_D=-1mA, V_{DS}=V_{GS}$
Gate-Body Leakage	I_{GSS}			100	nA	$V_{GS}=\pm 40V, V_{DS}=0V$
Zero Gate Voltage Drain Current	I_{DSS}			-10 -100	μA μA	$V_{DS}=-240V, V_{GS}=0$ $V_{DS}=-190V, V_{GS}=0V, T=125^{\circ}C$
On-State Drain Current	$I_{D(on)}$	-0.75	-1.0		A	$V_{DS}=-10V, V_{GS}=-10V$
Static Drain-Source On-State Resistance	$R_{DS(on)}$		7.1 8.8	9 11	Ω Ω	$V_{GS}=-10V, I_D=-200mA$ $V_{GS}=-3.5V, I_D=-100mA$
Forward Transconductance (1) (2)	g_{fs}	125			mS	$V_{DS}=-10V, I_D=-0.2A$
Input Capacitance (2)	C_{iss}		100	200	pF	$V_{DS}=-25V, V_{GS}=0V, f=1MHz$
Common Source Output Capacitance (2)	C_{oss}		18	25	pF	
Reverse Transfer Capacitance (2)	C_{rss}		5	15	pF	
Turn-On Delay Time (2)(3)	$t_{d(on)}$		8	15	ns	$V_{DD}=-50V, I_D=-0.25A,$ $V_{GEN}=-10V$
Rise Time (2)(3)	t_r		8	15	ns	
Turn-Off Delay Time (2)(3)	$t_{d(off)}$		26	40	ns	
Fall Time (2)(3)	t_f		20	30	ns	

(1) Measured under pulsed conditions. Width=300 μs . Duty cycle $\leq 2\%$ (2) Sample test.
(3) Switching times measured with 50 Ω source impedance and <5ns rise time on a pulse generator